

SGM621B Low Power, Low Noise, Rail-to-Rail Output, Instrumentation Amplifier

GENERAL DESCRIPTION

The SGM621B is a high accuracy, high voltage instrumentation amplifier, which is designed to set any gain from 1 to 10000 with one external resistor. The device works well in battery-powered applications due to the low power consumption of 1.3mA typical quiescent current. The SGM621B provides SOIC-8, MSOP-8 and TDFN-3×3-8L packages which are much smaller than discrete classical-three-OPAs circuits.

The SGM621B provides 120ppm (MAX) non-linearity and 150 μ V (MAX) low input offset voltage. The device also features low noise, low bias current and low power. The combination of these characteristics makes it a good choice for applications requiring excellent DC performance.

The SGM621B offers $6nV/\sqrt{Hz}$ low input voltage noise, $300fA/\sqrt{Hz}$ input current noise at 1kHz, and $0.4\mu V_{P-P}$ in the 0.1Hz to 10Hz band. It is suitable for pre-amplifier applications. The 10 μ s settling time to 0.01% makes SGM621B appropriate for multiplexed applications.

The SGM621B is available in Green SOIC-8, MSOP-8 and TDFN-3×3-8L packages. It is specified over the extended -40°C to +125°C temperature range.

FEATURES

- Single External Resistor Gain Set (Set Gain from 1 to 10000)
- Input Offset Voltage: 150µV (MAX)
- Input Bias Current: 15nA (TYP)
- Common Mode Rejection Ratio: 105dB (TYP) (G = 10)
- Input Voltage Noise: 6nV/√Hz at 1kHz
 0.1Hz to 10Hz Voltage Noise: 0.4µV_{P.P}
- Bandwidth: 140kHz (G = 100)
- Settling Time to 0.01%: 10µs (G = 100)
- Rail-to-Rail Output
- Support Single or Dual Power Supplies:
 4.6V to 36V or ±2.3V to ±18V
- Low Power Supply Current: 1.3mA (TYP)
- -40°C to +125°C Operating Temperature Range
- Available in Green SOIC-8, MSOP-8 and TDFN-3×3-8L Packages

APPLICATIONS

Precision Current Measurement
Pressure Measurement



PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
	SOIC-8	-40°C to +125°C	SGM621BXS8G/TR	SGM 621BXS8 XXXXX	Tape and Reel, 4000
SGM621B	MSOP-8	-40°C to +125°C	SGM621BXMS8G/TR	SGM621B XMS8 XXXXX	Tape and Reel, 4000
	TDFN-3×3-8L	-40°C to +125°C	SGM621BXTDB8G/TR	SGM 621BDB XXXXX	Tape and Reel, 4000

MARKING INFORMATION

NOTE: XXXXX = Date Code. Trace Code and Vendor Code.

)	<u>(XX)</u>	<u>(X </u>	
			Vendor Code
			Trace Code
			Date Code - Year

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, +V _S to -V _S	40V
Input Common Mode Voltage	±Vs
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility (1)(2)	
HBM	±7000V
CDM	±1000V

NOTES:

- 1. For human body model (HBM), all pins comply with ANSI/ESDA/JEDEC JS-001 specifications.
- 2. For charged device model (CDM), all pins comply with ANSI/ESDA/JEDEC JS-002 specifications.

RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range-40°C to +125°C

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

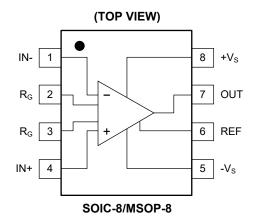
ESD SENSITIVITY CAUTION

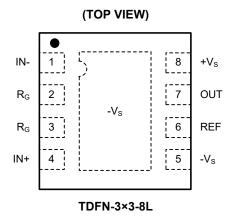
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

PIN CONFIGURATIONS





PIN DESCRIPTION

PIN	NAME	FUNCTION
1	IN-	Inverting Input Pin.
2, 3	R _G	Gain Setting Pin. The gain can be set by placing the resistor across R_G . $G = 1 + (49.4k\Omega/R_G)$.
4	IN+	Non-Inverting Input Pin.
5	-Vs	Negative Power Supply Pin.
6	REF	Voltage Reference Pin. A voltage source with low impedance can be placed to supply this terminal in order to shift the output level.
7	OUT	Output Pin.
8	+V _S	Positive Power Supply Pin.
Exposed Pad	-V _S	For TDFN-3×3-8L package, connect exposed pad to -V _S .

ELECTRICAL CHARACTERISTICS

 $(V_S = \pm 15V, R_L = 2k\Omega, Full = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ typical values are at } T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

PARAMETER	SYMBOL	CONDITIO	NS	TEMP	MIN	TYP	MAX	UNITS
Gain (G = 1 + $(49.4k\Omega/R_G)$)								
Gain Range					1		10000	
			G = 1	+25°C		0.01	0.1	
			G = 1	Full			0.15	
Gain Error ⁽¹⁾			G = 10	+25°C		0.15	0.3	
	GE	\\ = 10\\/ to \10\\/	G = 10	Full			0.6	%
	GE	$V_{OUT} = -10V \text{ to } +10V$	C - 400	+25°C		0.15	0.3	70
			G = 100	Full			0.6	
			C - 4000	+25°C		0.15	0.6	
			G = 1000	Full			0.8	
Gain Tomporature Coefficient			G = 1	Full		1		nnm/°C
Gain Temperature Coefficient			G > 1	Full		20		ppm/°C
			G = 1	+25°C		10	70	
			0-1	Full			100	
			G = 10	+25°C		10	70	
		V _{OUT} = -10V to +10V	G = 10	Full			100	
Non-Linearity		V _{OUT} 10V to +10V	C - 400	+25°C		10	70	ppm
			G = 100	Full			100	1
			0 4000	+25°C		20	120	
			G = 1000	Full			170	
Voltage Offset (Total RTI Error = '	V _{osi} + V _{oso} /(G)	I					
In a set Valta as		\\ - \\\\\\		+25°C		50	150	/
Input Offset Voltage	V _{osi}	V _S = ±5V (0 ±15V	$V_S = \pm 5V$ to $\pm 15V$				200	μV
Input Offset Voltage Drift	ΔV _{OSI} /ΔT			Full		0.2		μV/°C
				+25°C		400	1200	
Output Offset Voltage	Voso	$V_S = \pm 5V$ to $\pm 15V$		Full			1600	μV
Output Offset Voltage Drift	ΔV _{oso} /ΔT			Full		1.5		μV/°C
				+25°C	105	110		
			G = 1	Full	102	110		
				+25°C	125	130		1
Offset Referred to the Input			G = 10	Full	122	100		
vs. Supply	PSRR	$V_S = \pm 2.3 V \text{ to } \pm 18 V$		+25°C	128	140		dB
,			G = 100	Full	125	140		-
				+25°C	128	140		
			G = 1000	Full	125	140		-
Input Current				Full	123			
•				+25°C		15	25	
Input Bias Current	I _B			Full			35	nA
Average Temperature Coefficient of Input Bias Current	ΔΙ _Β /ΔΤ			Full		0.15		nA/°C
•				+25°C		5	20	_
Input Offset Current	Ios			Full			25	nA
Average Temperature Coefficient of Input Offset Current	ΔI _{OS} /ΔT			Full		0.05	-	nA/°C

NOTE: 1. Effects of external resistor R_{G} is not included.

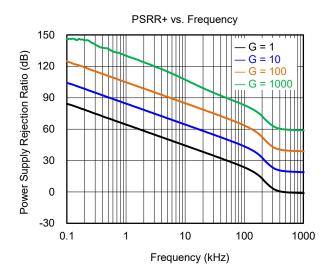
ELECTRICAL CHARACTERISTICS (continued)

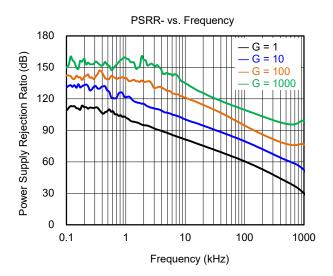
 $(V_S = \pm 15V, R_L = 2k\Omega, Full = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ typical values are at } T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

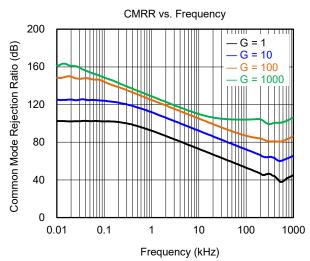
PARA	AMETER	SYMBOL	CONDITIO	NS	TEMP	MIN	TYP	MAX	UNITS	
Input		T	T		1	T		Т	ı	
Input	Differential	Z_{DIFF}			+25°C		10 4		GΩ p	
Impedance	Common Mode	Z _{CM}		+25°C		10 4		011 pi		
			V _s = ±2.3V to ±5V		+25°C	(-V _S) + 1.9		(+V _S) - 1.2		
Input Voltage R	ange		V5 - 12.0V to 10V		Full	$(-V_S) + 2.1$		(+V _S) - 1.3	V	
input voltage it	ungo		$V_{\rm S} = \pm 5 \text{V to } \pm 18 \text{V}$		+25°C	(-V _S) + 1.9		(+V _S) - 1.4	ľ	
			V ₃ = 20 V to = 10 V		Full	$(-V_S) + 2.1$		(+V _S) - 1.4		
				G = 1	+25°C	70	85			
					Full	67				
				G = 10	+25°C	90	105			
	Rejection Ratio	CMRR	V _{CM} = -10V to +10V		Full	87			dB	
with 1kΩ Source	e imbalance			G = 100	+25°C	103	120			
					Full	100	400			
			G = 1000	+25°C	103	120				
Reference Inpu	.4				Full	100				
Reference Inpu		R _{REF}			+25°C		18		kΩ	
Neierence inpu	i i tesisiance	TREF	$V_{IN+} = V_{IN-} = 0V, V_{REF} = 0V$		-			40	KZZ	
Reference Input	t Current	I_{REF}			+25°C Full		30	40 50	μΑ	
Output Charac	teristics				Full			50		
4					+25°C		310	400		
		V_{OH}	$V_S = \pm 18V$, $R_L = 2k\Omega$		Full			600		
Output Voltage Swing				+25°C		150	220	mV		
		V _{OL}	$V_S = \pm 18V$, $R_L = 2k\Omega$		Full				300	
					+25°C	19	24			
Short-Circuit Cu	ırrent	I _{SC}	I_{SC} $V_S = \pm 2.3 V$ to $\pm 18 V$, $R_L = 50 \Omega$ to $V_S/2$		Full	14			mA	
Power Supply		1	•		•					
Quiescent Curre	ent	ΙQ	$V_{\rm S} = \pm 2.3 \text{V to } \pm 18 \text{V, } I_{\rm OUT}$	= ΛΔ	+25°C		1.3	1.7	mA	
Quiescent Curre	SIIC	IQ.	V _S - ±2.3V to ±16V, I _{OUT} - UA		Full			2.2	mA	
Dynamic Resp	onse	T	T		1	Т		Т	ı	
				G = 1	+25°C		3900			
Small-Signal -3	dB Bandwidth	BW		G = 10	+25°C		1000		kHz	
Oman-Olynar -O	ub bandwidth	DVV		G = 100	+25°C		140		KIIZ	
			G = 1000		+25°C		17			
Slew Rate		SR	V _{OUT} = 1V _{P-P} Step	G = 1	+25°C		1.2		V/µs	
				G = 1 to 100	+25°C		10			
Settling Time to	0.01%	ts	$V_{OUT} = 10V_{P-P}$ Step	G = 1000	+25°C		51		μs	
Noise		I			ı	I		I	I	
Input Voltage N	oise Density	e _{ni}	f = 1kHz		+25°C		6		nV/√Hz	
Output Voltage	Noise Density	e _{no}	f = 1kHz		+25°C		80		nV/√Hz	
	-			G = 1	+25°C		6			
				G = 10	+25°C		1		-	
0.1Hz to 10Hz \	/oltage Noise, RTI		f = 0.1Hz to 10Hz		+25°C		0.4		μV _{P-P}	
				G = 100 G = 1000	+25°C		0.4		-	
Innuit Criment N	oice Density DT		f = 41/11=	G = 1000	1				£0.1/11	
•	oise Density, RTI	i _n	f = 1kHz		+25°C		300		fA/√Hz	
U.1Hz to 10Hz (Current Noise, RTI		f = 0.1Hz to 10Hz		+25°C		15		pA _{P-P}	

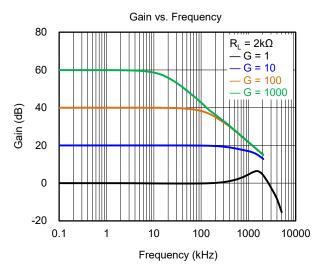
TYPICAL PERFORMANCE CHARACTERISTICS

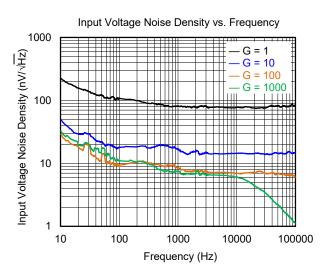
At $T_A = +25$ °C, $V_S = \pm 15$ V, unless otherwise noted.

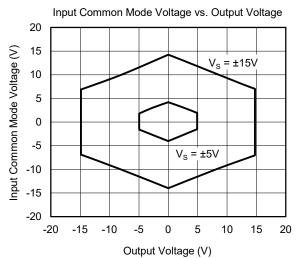






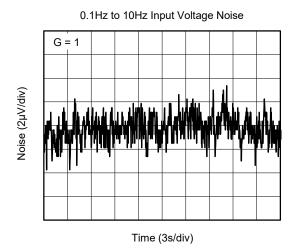


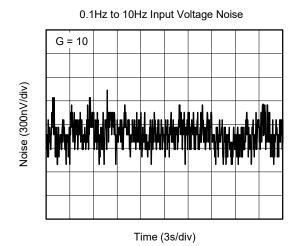


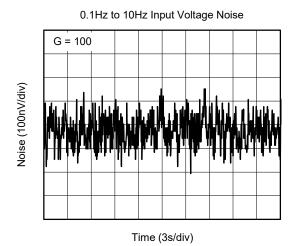


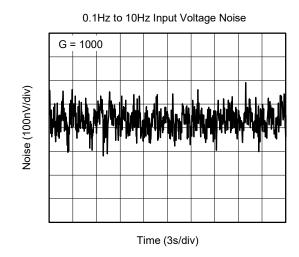
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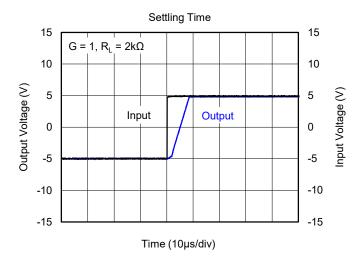
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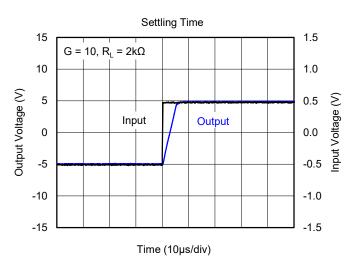






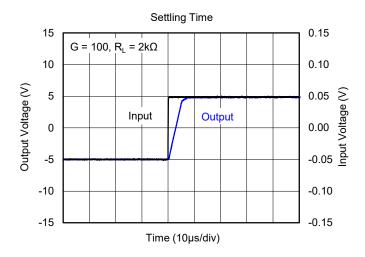


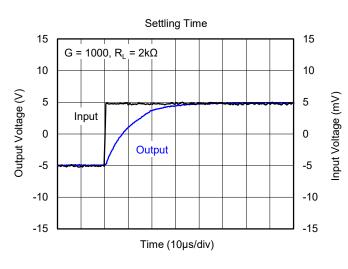


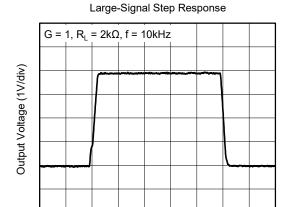


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

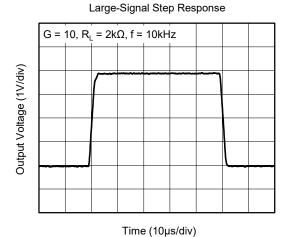
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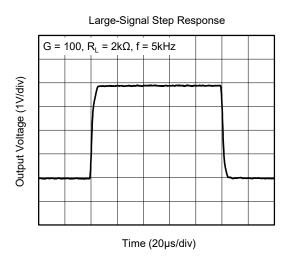


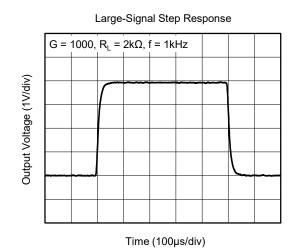








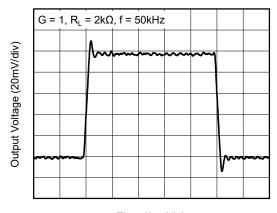




TYPICAL PERFORMANCE CHARACTERISTICS (continued)

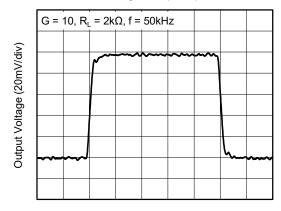
At $T_A = +25$ °C, $V_S = \pm 15$ V, unless otherwise noted.





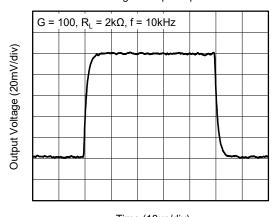
Time (2µs/div)

Small-Signal Step Response



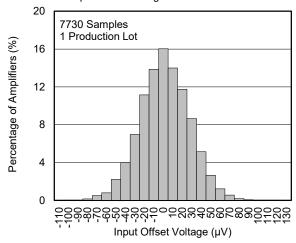
Time (2µs/div)

Small-Signal Step Response

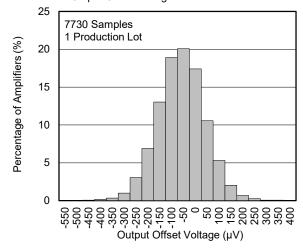


Time (10µs/div)

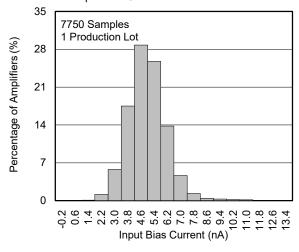
Input Offset Voltage Production Distribution



Output Offset Voltage Production Distribution



Input Bias Current Production Distribution



OPERATION THEORY

The SGM621B is modified with the classic three-op-amp and it is a holistic instrumentation amplifier.

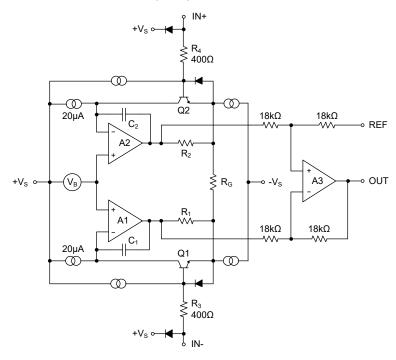


Figure 1. Simplified Schematic

The high precision input is provided by the two input transistor Q1 and Q2 (Figure 1) and this results in 10 × lower bias current of the input pins. The constant collector current of Q1 and Q2 is maintained by the two loops Q1-A1-R1 and Q2-A2-R2, so the input voltage is impressed across the gain setting resistor $R_{\rm G}$ of the amplifier. The differential gain from A1/A2 outputs can be expressed by $G = 1 + (R_1 + R_2)/R_{\rm G}$. The unity-gain subtractor (A3) can reject the common mode signal so that SGM621B produces a single-ended output with REF pin biased.

The transconductance of the pre-amplifier is determined by the resistance of R_{G} . The transconductance will increase gradually to that of the input transistors if the resistance of R_{G} is reduced for larger gains. The important benefits are shown below:

• Boosting the open-loop gain can also increase the programmed gain, so that the related error of gain is reduced.

- The gain-bandwidth product which is determined by the two capacitors C₁, C₂ and the transconductance of the pre-amplifier can increase with programmed gain, so that the frequency response is enhanced.
- Reducing the input voltage noise to $6nV/\sqrt{Hz}$, and it is determined by the base resistance and the collector current of the input.

The integrated resistors (R_1 and R_2) inside the SGM621B are set to 24.7k Ω , so that the gain can be programmed with the external resistor R_G .

The equation of gain is shown as below:

$$G = \frac{49.4k\Omega}{R_G} + 1$$

$$R_G = \frac{49.4k\Omega}{G - 1}$$

APPLICATION INFORMATION

Pressure Measurement

SGM621B is widely used in the application of bridge, such as measuring the pressure in weigh scales. It is also suitable for detecting the pressure sensor with higher resistance due to high input impedance.

Figure 2 shows the pressure transducer bridge of $5k\Omega$ which is powered by a 5V single supply. In such a circuit, the bridge consumes only 1mA. The buffered voltage divider and SGM621B can condition the output signal with typical 3.3mA supply current.

The advantage of small size for SGM621B is attractive for the transducers of pressure. Because of the low noise and drift, it can also be used in the application of diagnostic non-invasive blood pressure measurement.

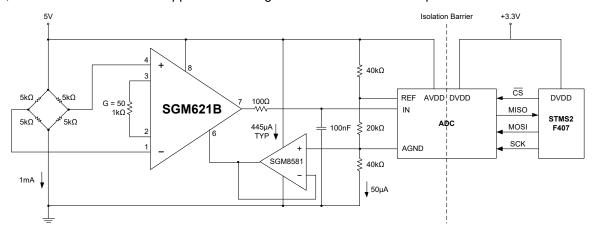


Figure 2. The Operation of the Pressure Monitor Circuit with 5V Single Supply

Medical ECG Amplifier

Because of the advantage of low current noise, SGM621B can be used in ECG monitors (Figure 3) where the source resistances can reach $1M\Omega$ or higher. It is the best choice to use SGM621B in the battery-powered data recorders as it can operate on the condition of low supply voltage, low power and space-saving packages.

Moreover, for better performance, combining with the advantages of low voltage noise, low current and low bias currents can enhance the dynamic range of SGM621B.

The stability of the right leg drive loop can be maintained by the capacitor C₁. Moreover, for protecting the patient from the possible harm, the isolation safeguards should be added between the patient and the circuit part.

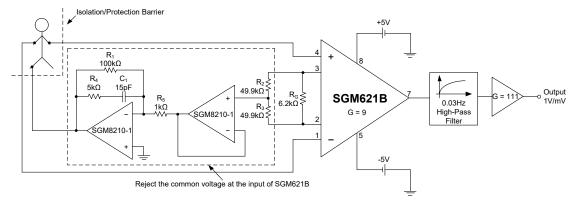


Figure 3. The Circuit of Medical ECG Monitor

APPLICATION INFORMATION (continued)

Precision V-I Converter

It's easy to realize a precision current source (Figure 4) utilizing one SGM621B, another operational amplifier and two resistors. To obtain a better CMRR of SGM621B, a buffer should be placed between the REF pin and the OUT pin of the amplifier. The equation which is shown in Figure 4 illustrates the output current of the circuit.

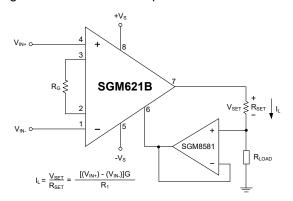


Figure 4. Precision Voltage-to-Current Converter

Input and Output Offset Voltage

Two main sources which are error of input and output result in the low errors of SGM621B. When referred to the input, the output error should be divided by the gain of the instrumentation amplifier. From the equations which are shown as below, the input error takes a leading position at large gains while the output error takes a leading position at small gains.

Total Error Referred to Input (RTI) = Input Error + (Output Error/G)

Total Error Referred to Output (RTO) = (Input Error × G) + Output Error

Terminal of Reference

Potential of the reference terminal defines the zero output voltage. It becomes extremely useful while the load is not tied to the precise ground of the rest of the system. The reference terminal provides one way to bias a precise voltage to the output, and the reference voltage should be in the range of 2V within the supply voltages. On top of these, to keep better CMRR, the parasitic resistor at this pin should be low.

Selection of Gain

The gain of the instrumentation amplifier is determined by the external resistor $R_{\rm G}.$ The accuracy of the external resistor $R_{\rm G}$ is important as it may influence the error of gain. It is recommended that selecting the resistor with 0.1% or 1% precision is a good choice. The following table shows the gain effect with the selection of 1% or 0.1% precision resistor. Also, leaving the pin 2 and pin 3 (the place of $R_{\rm G}$) open can make the gain of SGM621B equals to 1.

$$R_{G} = \frac{49.4k\Omega}{G - 1}$$

As mentioned before, the gain error can be minimized by equivalent parasitic resistor in series with $R_{\rm G}$. Moreover, low TC of 1ppm/°C is required for the selection of $R_{\rm G}$ to avoid the gain drift of SGM621B.

Table 1. Different Values for Gain Resistor

1% STD Table Value of $R_G(\Omega)$	Calculated Gain	0.1% STD Table Value of $R_G(\Omega)$	Calculated Gain
49.9k	1.990	49.3k	2.002
12.4k	4.984	12.4k	4.984
5.49k	9.998	5.49k	9.998
2.61k	19.93	2.61k	19.93
1.00k	50.40	1.01k	49.91
499	100.0	499	100.0
249	199.4	249	199.4
100	495.0	98.8	501.0
49.9	991.0	49.3	1003.0

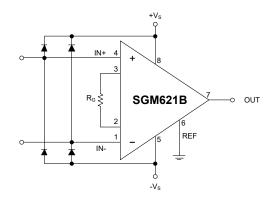


Figure 5. Diode for Protecting V_{IN} from Larger than V_S

APPLICATION INFORMATION (continued)

RF Interference

One of the characteristics of instrumentation amplifier is rectifying the small signal which is out of the band. This kind of disturbance can be described as the small biased voltage. All of the high frequency components can be filtered by the R-C network which is placed in the input position of the instrumentation amplifier, as shown in Figure 6. The following equation shows the equation of filtering frequency for the differential and common mode part of the input signal.

FilterFreq_{DIFF} =
$$\frac{1}{2\pi R(2C_D + C_C)}$$

FilterFreq_{CM} = $\frac{1}{2\pi RC_C}$

 $C_D \ge 10C_C$ is required in the above equation.

The capacitor C_D influences the quality of the differential signal, while C_C influences the quality of the common mode signal. The common mode rejection ratio would be reduced if the $R \times C_C$ is mismatched. To reduce this negative influence and obtain a good CMRR, it is recommended that the capacitance of C_D should be 10 times larger than C_C . To conclude, the larger the ratio of C_D : C_C is, the less negative influence to the circuit.

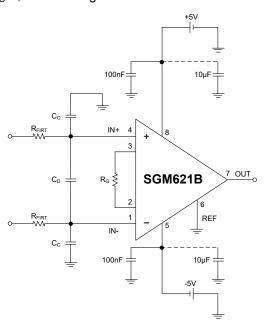


Figure 6. One Method to Reduce the Interference of RF

Common Mode Rejection

The common mode rejection ratio of the instrumentation amplifier is high as it can measure the differential signal between the two inputs when both IN+ and IN- increase or decrease equally. Also, this specification can be defined in the whole range of input voltage.

To obtain a best CMRR, it is recommended that the REF pin should be connected to a low impedance input and the difference of impedance between two inputs should be as small as possible. Also, using shielded cable can effectively reduce the noise of the circuit, and it should be driven properly for better value of CMRR. The following two figures (Figure 7 and Figure 8) illustrate the method to increase the CMRR for alternating circuit by bootstrapping the capacitance of the shielded cable, and this kind of method can also reduce the mismatching of capacitance at the inputs.

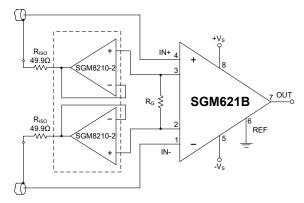


Figure 7. Differential Input Shield Driving

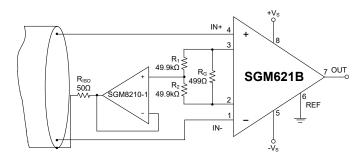


Figure 8. Common Mode Input Shield Driving

APPLICATION INFORMATION (continued)

Isolation of Grounding

For solving the problems of grounding, REF pin should be connected to the "local ground" as the output of the instrumentation amplifier is biased with V_{REF} .

Because of the noisy environment of the digital circuit, the component of data-acquisition such as Analog Digital Converter (ADC) has two pins which are AGND and DGND. Also, the isolation can be made by using a single line or 0Ω resistor. However, each returns of ground should be separated so that the current flow from the sensitive point could be minimized. Also, the ground returns between analog and digital should be tied together with one point, which is shown in ADC part of Figure 9.

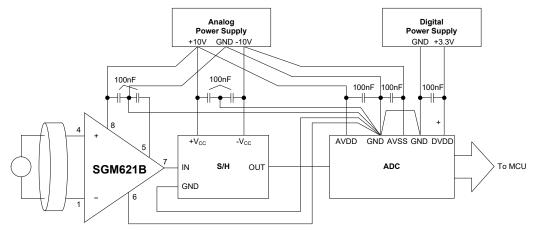


Figure 9. Isolation of Grounding

Return of Grounding for IB

The bias current (I_B) at the inputs is needed for operating and biasing the transistor at the input stage of the instrumentation amplifier, so it is also necessary to design a ground return path for the bias current. For example, for operating the floating inputs of the amplifier (see Figure 10 \sim 12), such as AC-coupled transformer, there should be an electrical line between the input and the ground for ground return of bias current.

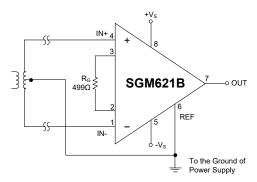


Figure 10. Return of Grounding for I_B with Transformer-Coupled Inputs

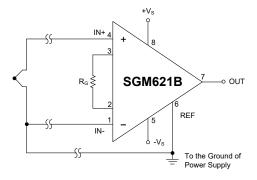


Figure 11. Return of Grounding for I_B with Thermocouple Inputs

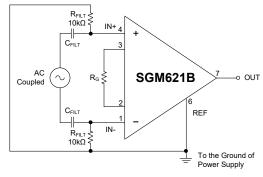


Figure 12. Return of Grounding for I_B with AC-Coupled Input

Low Power, Low Noise, Rail-to-Rail Output, Instrumentation Amplifier

SGM621B

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

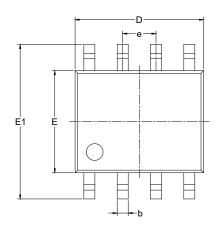
Changes from Original (JANUARY 2025) to REV.A

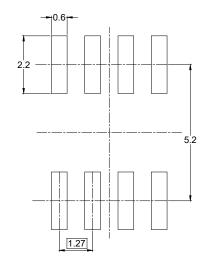
Page

Changed from product preview to production data.......All

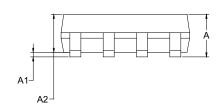


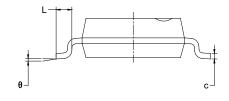
PACKAGE OUTLINE DIMENSIONS SOIC-8





RECOMMENDED LAND PATTERN (Unit: mm)





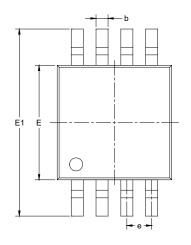
Symbol	-	nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.27 BSC		0.050 BSC		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

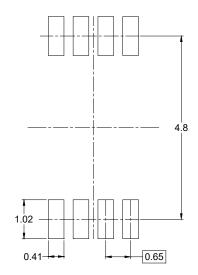
- NOTES:

 1. Body dimensions do not include mode flash or protrusion.

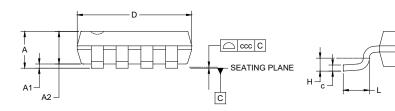
 2. This drawing is subject to change without notice.

PACKAGE OUTLINE DIMENSIONS MSOP-8





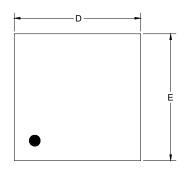
RECOMMENDED LAND PATTERN (Unit: mm)

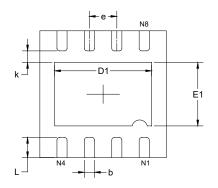


Cumbal	Dimensions In Millimeters						
Symbol	MIN	NOM	MAX				
Α	-	-	1.100				
A1	0.000	-	0.150				
A2	0.750	-	0.950				
b	0.220	-	0.380				
С	0.080	-	0.230				
D	2.800	-	3.200				
E	2.800	-	3.200				
E1	4.650	5.150					
е		0.650 BSC					
L	0.400	-	0.800				
Н	0.250 TYP						
θ	0°	8°					
ccc		0.100					

- This drawing is subject to change without notice.
 The dimensions do not include mold flashes, protrusions or gate burrs.
- 3. Reference JEDEC MO-187.

PACKAGE OUTLINE DIMENSIONS TDFN-3×3-8L

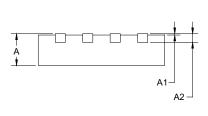




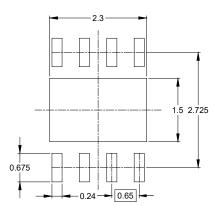
TOP VIEW







SIDE VIEW



RECOMMENDED LAND PATTERN (Unit: mm)

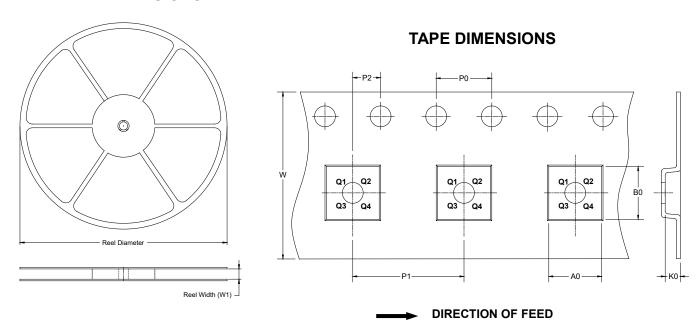
Symbol		nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
А	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	REF	0.008	REF	
D	2.900	3.100	0.114	0.122	
D1	2.200	2.400	0.087	0.094	
E	2.900	3.100	0.114	0.122	
E1	1.400	1.600	0.055	0.063	
k	0.200	MIN	0.008	MIN	
b	0.180	0.300	0.007	0.012	
е	0.650 TYP		0.026	TYP	
L	0.375 0.575		0.015	0.023	

NOTE: This drawing is subject to change without notice.



TAPE AND REEL INFORMATION

REEL DIMENSIONS

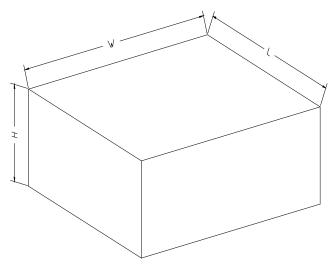


NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOIC-8	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
MSOP-8	13"	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
TDFN-3×3-8L	13"	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)			Pizza/Carton	
13″	386	280	370	5	DD0002